

SILICON BRIDGE RECTIFIERS

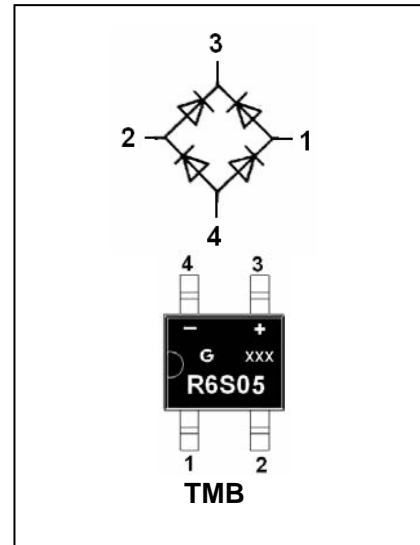
TMBR6S05

FEATURES



Lead-free

- Ultra Low leakage current $I_R < 2\mu A$, $T_a = 125^\circ C$
- No solder used, Real fully in line with lead free
- Package Thickness is 1.2mm
- High ESD >12KV (HBM MODEL)
- Plastic material has U/L flammability classification 94V-0
- High temperature soldering guaranteed:
260°C/10s (Reflow)
350°C/3s (Manual welding)



APPLICATION

- Small signal rectifier devices.

MAXIMUM RATING (operating temperature range applies unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	600	V
V_{RMS}	RMS Voltage	420	V
V_{DC}	DC Blocking Voltage	600	V
$I_{F(AV)}$	Average Forward Rectified Current @ $T_A = 25^\circ C$	0.5	A
I_{FSM}	Peak Forward Surge Current 8.3ms Single Half Sine-wave	12	A
$R_{\theta JA}$	Thermal Resistance	200	°C/W
$T_j T_{stg}$	Operating Junction and Storage Temperature Range	-55 to +150	°C

ELECTRICAL CHARACTERISTICS @ $T_a = 25^\circ C$ unless otherwise specified

Symbol	Parameter	Test conditions	Value	Unit
I_R	Reverse Current	$V_{RM} = V_{RRM}, T_A = 25^\circ C$	0.5	μA
		$V_{RM} = V_{RRM}, T_A = 125^\circ C$	2.0	
V_F	Forward Voltage	$I_F = 0.25A, T_A = 25^\circ C$	1.0	V

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PACKAGE OUTLINE

Plastic surface mounted package

TMB

